a2

8. (twice amended) The wafer prober according to claim 1 [which comprises a ceramic substrate and a conductor layer formed on the surface thereof], wherein said conductor layer is composed of porous material.

Please add the following claims.

a3

--9. The wafer prober according to claim 2, wherein said ceramic substrate is equipped with a temperature control means.

10. The wafer prober according to claim 9, wherein said temperature control means is a heating element.

11. A ceramic substrate for a wafer prober which has a conductor layer formed on the surface thereof, wherein said ceramic substrate is composed of at least one selected from the group consisting of nitride ceramics, carbide ceramics and oxide ceramics.

12. A ceramic substrate for a wafer prober which has a conductor layer formed on the surface thereof, wherein in said ceramic substrate at least one conductor layer is formed.

drift as claim 2

13. The ceramic substrate for a wafer prober according to claim 11, wherein said ceramic substrate is equipped with a temperature control means.

3 14. The ceramic substrate for a wafer prober according to claim 12, wherein said ceramic substrate is equipped with a temperature control means.

4 15. The ceramic substrate for a wafer prober according to claim 13, wherein said temperature control means is a heating element.

4 16. The ceramic substrate for a wafer prober according to claim 14, wherein said temperature control means is a heating element.

5 17. A ceramic substrate according to claim 11, wherein said ceramic substrate is equipped with a Peliter device.

6 18. A ceramic substrate according to claim 11, wherein on said ceramic substrate channels are formed.

7 19. The ceramic substrate for a wafer prober according to claim 14, wherein said channels formed on the surface of said ceramic substrate are provided with air suction holes.

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6 20. A ceramic substrate according to claim 11, wherein said conductor layer is composed of porous material.--